



#### 40V N-Channel Enhancement Mode MOSFET

Voltage 40 V Current 4.3A

#### **Features**

- RDS(ON), VGS@10V, ID@4.3A<42m $\Omega$
- RDS(ON), VGS@4.5V, ID@3.9A<51mΩ
- Advanced Trench Process Technology
- Specially Designed for switch Load, PWM applications, and solid-state relays relay
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

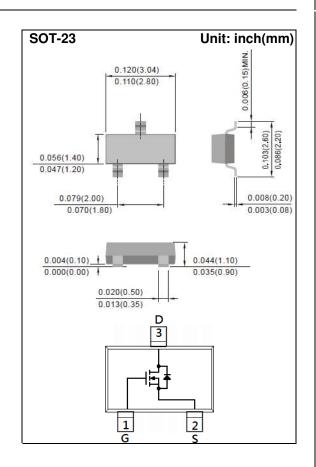
### **Mechanical Data**

Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.0084 grams

Marking: A40



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	4.3	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	17.2	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W
	Derate above 25°C		10	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)		$R_{\theta JA}$	100	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_D$ =4.3A	-	35	42	mΩ
		$V_{GS}$ =4.5V, $I_{D}$ =3.9A	-	44	51	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =20V, I <sub>D</sub> =4.3A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	4.8	-	
Gate-Source Charge	$Q_gs$		-	1.4	-	nC
Gate-Drain Charge	$Q_{gd}$		-	1.8	-	
Input Capacitance	Ciss	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1.0MHZ	-	410	-	pF
Output Capacitance	Coss		-	50	-	
Reverse Transfer Capacitance	Crss		-	30	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =20V, $I_{D}$ =3.5A, $V_{GS}$ =10V, $R_{G}$ =1 $\Omega$ (Note 1,2)	-	4	-	ns
Turn-On Rise Time	tr		-	30	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	15	-	
Turn-Off Fall Time	tf		-	8	-	
Drain-Source Diode						
Maximum Continuous Drain-Source		l <sub>s</sub>			1.0	А
Diode Forward Current	IS		_	-		
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.78	1.2	V
Reverse Recovery Time	trr	$V_{GS}$ =0V, $I_{S}$ =3.5A $dI_{F}/dt$ =100A/us	-	10.2	-	ns
Reverse Recovery Charge	Qrr		-	5.5	-	nC

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

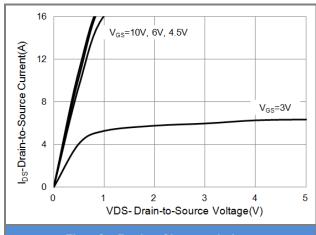
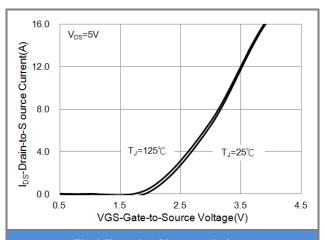


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

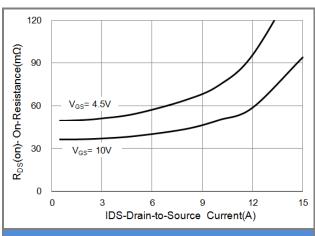


Fig.3 On-Resistance vs. Drain Current

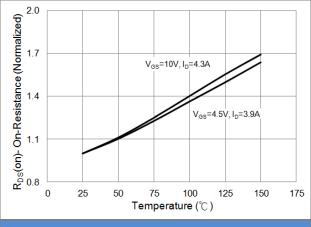
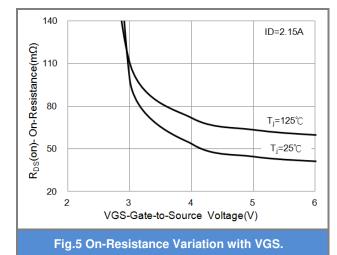
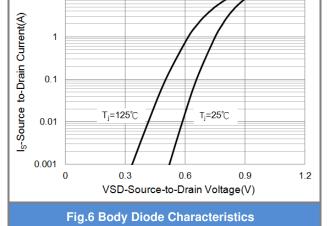


Fig.4 On-Resistance vs. Junction temperature





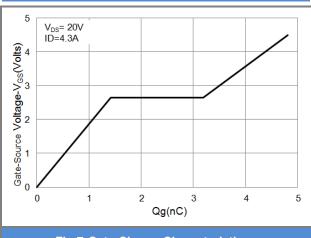
June 5,2015-REV.01 Page 3

10





### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

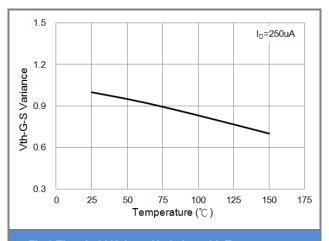


Fig.8 Threshold Voltage Variation with Temperature.

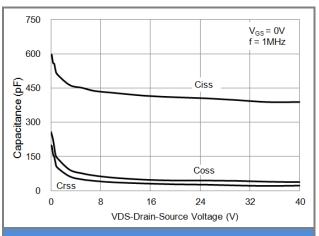


Fig.9 Capacitance vs. Drain-Source Voltage.

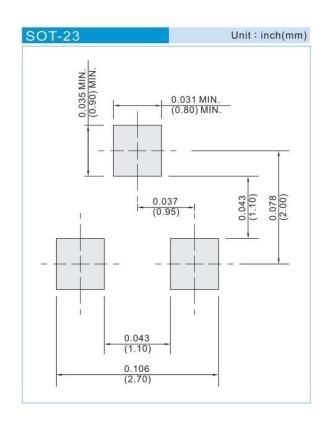




### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing type	Marking	Version
PJA3440_R1_00001	SOT-23	3K pcs / 7" reel	A40	Halogen free
PJA3440_R2_00001	SOT-23	12K pcs / 13" reel	A40	Halogen free

### **MOUNTING PAD LAYOUT**







### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
  responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
  representation or warranty that such applications will be suitable for the specified use without further testing or
  modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.